



PTO-1449 Information Disclosure Citation in an Application		Application No. 10/757,092		Applicant(s): Ted Johansson et al.	
		Docket Number 068758.0157		Group Art Unit 1762	

U.S. PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
OL	1	4,988,632	01-29-91	Pfiester	437	31	01-02-90
OL	2	5,213,989	05-25-93	Fitch et al.	437	31	06-24-92
OL	3	5,266,504	11-30-93	Blouse et al.	437	31	03-26-92
OL	4	5,502,330	03-26-96	Johnson et al.	257	588	06-07-95
OL	5	5,592,017	01-07-97	Johnson	257	554	06-07-95
OL	6	5,616,508	04-01-97	Johnson	438	350	01-09-95
OL	7	6,077,752	06-20-00	Norström	438	309	05-19-98
OL	8	6,255,183	07-03-01	Schmitz et al.	438	309	04-22-98

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
OL	9	SE0103726-6	07-01-03	SWEDEN	H01L	21/331	x	
OL	10	WO 97/19465	05-29-97	PCT	H01L	21/316	x	

NON-PATENT DOCUMENTS			
		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
OL	11	B. Tillack et al.; "Monitoring of deposition and dry etching of Si/SiGe multiple stacks"; J. Vac. Sci. Technol. B14(1)9, pp. 1184-1198	Jan/Feb 1996
OL	12	Tsu-Jae King et al.; "A Polycrystalline-Si _{1-x} Ge _x -GATE CMOS Technology"; Center for Integrated Systems, Stanford University, Stanford, CA	4/1990
OL	13	E. Josse, et al.; "High performance 0.1 μpmosfets with optimized poily-Si and poly-SiGe gates"	
OL	14	J.A. Babcock et al.; "Precision electrical Trimming of Very Low TCR Poly-SiGe Resistors" IEEE Electron Device Letters. Vol. 21, No. 6	June, 2000
OL	15	S. Wolf et al.; "for the VLSI Era"; volume 1 – Process Technology; p. 565-567	
OL	16	D. L. Hareme; et al.; "Si/SiGe Epitaxial-Base Transistors-Part II: Process Integration and Analog Applications" IEEE Transactions on Electron Devices, Vol. 42, No. 3	March 1995
OL	17	T.H. Ning, et al.; "Self-Aligned NPN Bipolar Transistors"; International Electron Devices Meeting; Washington, D.C.	December 1980

EXAMINER 	DATE CONSIDERED 6/16/04
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.